

*CLAIM AMENDMENTS*

1. (Currently Amended) A semiconductor device ~~on which comprising:~~  
a plurality of semiconductor elements, each semiconductor element having first and second main electrodes and a control electrode ~~are arranged, comprising:~~  
a semiconductor substrate having one a first principal plane on which the first and second main electrodes and the control electrode are ~~formed located;~~  
~~a film which is formed over the first main electrode and the control electrode so as to insulate, insulating the first main electrode and the control electrode from the second main electrode, and is made of a polymer material with a low dielectric constant; and~~  
~~a chip surface electrode formed over the film and the second main electrode and connected to a ground potential, wherein the second main electrode is provided with the ground potential through the chip surface electrode.~~
2. (Currently Amended) ~~A~~ The semiconductor device according to claim 1, ~~wherein~~  
~~including a first pad connected to the first electrode and a second pad connected to the second electrode~~ ~~are formed and located on a second~~ principal plane ~~on the, opposite side of the first~~ principal plane ~~of the semiconductor~~ on which the electrodes ~~of the semiconductor substrate~~ are formed located.
3. (Currently Amended) ~~A~~ The semiconductor device according to claim 1, wherein  
the semiconductor substrate is ~~made from one of SiC or~~ and sapphire.
4. (Currently Amended) A semiconductor device ~~on which comprising:~~  
a plurality of semiconductor elements, each semiconductor element having first and second main electrodes and a control electrode ~~are formed, comprising:~~  
a semiconductor substrate having one a first principal plane on which the first and second main electrodes and the control electrodes are ~~formed located;~~ and  
a protecting film ~~formed~~ over the first and second main electrodes and the control electrodes, and made of a polymer material with a low dielectric constant.
5. (Currently Amended) A semiconductor device ~~on which comprising:~~  
a plurality of semiconductor elements, each semiconductor element having first and second main electrodes and a control electrode ~~are formed, comprising:~~

a semiconductor substrate having ~~one~~ a first principal plane on which the first and second main electrodes and the control electrodes are ~~formed~~ located;

a metal layer ~~which is formed~~ on a second principal plane ~~on the~~, opposite ~~side of~~ the first principal plane of the semiconductor substrate and which is grounded;

a film ~~formed~~ over the first and second main electrodes and the control electrodes and made of a polymer material with a low dielectric constant; and

a surface layer ~~which is formed~~ on the film made of a polymer material with a low dielectric constant and which is ~~made of~~ the same material as ~~that of~~ the grounded metal layer.

6. (Currently Amended) ~~A~~ The semiconductor device according to claim 5, wherein the surface layer is electrically connected to the grounded metal layer.